V. Kendre *et al*., "CdTe films by Elemental Vapor Transport," *2013 IEEE 39th Photovoltaic Specialists Conference (PVSC)*, Tampa, FL, USA, 2013, pp. 1-4, doi: 10.1109/PVSC.2013.6744411.

The electro-optical properties of CdTe films deposited by Elemental Vapor Transport (EVT) are being investigated. The EVT process, unlike most processes currently used for the deposition of CdTe thin films, allows for the creation of excess Cd or excess Te conditions during the deposition, which can be used to influence the formation of defects and improve doping in CdTe. Using resistivity measurements, it has been demonstrated that the Cd/Te ratio used during the deposition process influences the incorporation of Cu in CdTe. Photoluminescence measurements have shown that the Cd/Te ratio also influences the formation of defect complexes in CdTe. Junctions formed with CdS suggest that the conductivity of CdTe can be adjusted p- or n-type by creating Te or Cd-rich conditions respectively. Structurally, the EVT-CdTe films have been found to be densely packed and highly oriented.